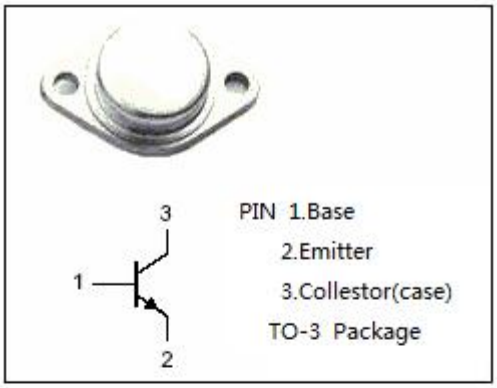
isc Silicon NPN Power Transistors — BUY70A

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 400V(Min)
- Low Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 5.0V(Max.)@ I_C= 4A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

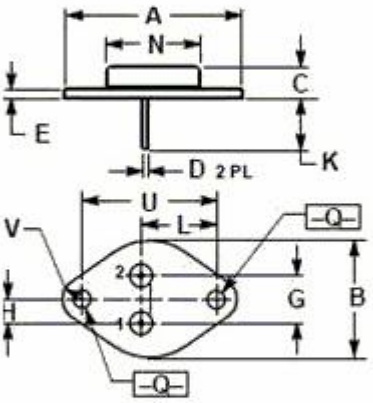


APPLICATIONS

- Designed for switching mode power supplies, inverters, and CRT scanning systems.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1000	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-peak	15	A
I_B	Base Current-Continuous	3.0	A
P_C	Collector Power Dissipation @T_C=25℃	75	W
T_j	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.3	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA; I_B= 0	400			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	1000			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 10mA; I_C= 0	8			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 4A; I_B= 0.8A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 4A; I_B= 0.8A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 1000V; I_E= 0			1.0	mA
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}= 10V	15			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V		6		MHz
C_{OB}	Collector Output Capacitance	I_E= 0; V_{CB}= 20V			150	pF
t_f	Fall Time	I_C= 4A; I_{B1}= -I_{B2}= 0.8A; V_{CC}= 40V			1.0	μs